A METHOD OF REVEALING CRYSTALLINE DEFECTS IN A BULK SUBSTRATE

A B S T R A C T

A method of pre-emptively revealing crystalline defects in a bulk silicon substrate is described, said defects being such that they would appear subsequently if said substrate were to be used in a method of lifting and transferring layers and be recycled at least three times. This method is remarkable in that it comprises a step consisting in:

· subjecting said bulk substrate to a heat treatment termed a "revealing heat treatment", that is carried out in a non-reducing atmosphere at a temperature in the range from about 500°C to 1300°C.